

PATENT  
Attorney Docket No. ASC-049C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Fitzgerald CONFIRMATION NO.: 8754  
SERIAL NO.: 10/774,890 GROUP NO.: 2818  
FILING DATE: February 9, 2004 EXAMINER: Tran, Mai Huong  
TITLE: RELAXED SiGe PLATFORM FOR HIGH SPEED CMOS  
ELECTRONICS AND HIGH SPEED ANALOG CIRCUITS

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98 (a)(2)(i), only copies of the foreign patent documents and non-patent publications are enclosed.

**REMARKS**

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**

- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or
- ☐ (3) after the mailing date of a **final action or notice of allowance** but before the payment of the issue fee, **AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein.

*The following applications have been considered*  
Applicant wishes to inform the Examiner about the following co-pending patent applications and Office actions issued therein:

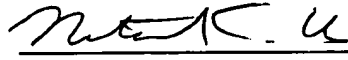
- 1) U.S. Serial No. 09/611,024 (Docket No. ASC-023) filed on 06/07/2000, by Fitzgerald;
- 2) U.S. Serial No. 10/611,739 (Docket No. ASC-044C1) filed on 07/01/2003, by Fitzgerald *et al.*;
- 3) U.S. Serial No. 10/802,185 (Docket No. ASC-025DVC1) filed on 03/17/2004, by Cheng *et al.*;
- 4) U.S. Serial No. 10/802,186 (Docket No. ASC-025DV2C1) filed on 03/17/2004, by Cheng *et al.*;
- 5) U.S. Serial No. 10/826,156 (Docket No. ASC-023C2) filed on 04/16/2004, by Fitzgerald;
- 6) U.S. Serial No. 10/854,556 (Docket No. ASC-054C1), filed May 26, 2004, by Fitzgerald;
- 7) U.S. Serial No. 09/884,817 (Docket No. ASC-043), filed June 19, 2001 by Fitzgerald *et al.*;
- 8) U.S. Serial No. 10/022,689 (Docket No. ASC-023DVC2), filed December 17, 2001 by Fitzgerald;
- 9) U.S. Serial No. 09/906,534 (Docket No. ASC-054), filed July 16, 2001 by Fitzgerlad;
- 10) U.S. Serial No. 09/906,533 (Docket No. ASC-052), filed July 16, 2001 by Fitzgerald;
- 11) U.S. Serial No. 10/005,274 (Docket No. ASC-043CP), filed December 4, 2001 by Fitzgerald *et al.*;
- 12) U.S. Serial No. 10/116,559 (Docket No. ASC-026), filed April 4, 2002 by Cheng *et al.*;
- 13) U.S. Serial No. 10/172,542 (Docket No. ASC-057), filed June 14, 2002 by Hammond *et al.*;
- 14) U.S. Serial No. 10/266,399 (Docket No. ASC-043C1), filed October 8, 2002 by Fitzgerald *et al.*;
- 15) U.S. Serial No. 10/253,361 (Docket No. ASC-018), filed September 24, 2002 by Braithwaite *et al.*;
- 16) U.S. Serial No. 10/389,003 (Docket No. ASC-019), filed March 14, 2003 by Fitzgerald *et al.*;
- 17) U.S. Serial No. 10/264,935 (Docket No. ASC-008), filed October 4, 2002 by Lochtefeld *et al.*;
- 18) U.S. Serial No. 10/456,103 (Docket No. ASC ASC-008C), filed June 6, 2003 by Lochtefeld *et al.*;
- 19) U.S. Serial No. 10/456,708 (Docket No. ASC ASC-008B), filed June 6, 2003 by Lochtefeld; and
- 20) U.S. Serial No. 10/625,018 (Docket No. ASC-043C2), filed by Fitzgerald *et al.*

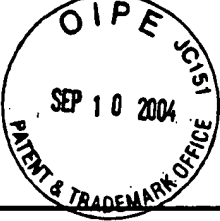
It is respectfully requested that the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: Sept-8, 2004  
Reg. No. 44,381

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<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>  				<b>ATTY DOCKET NO.:</b> ASC-049C1  <b>APPLICANT:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/774,890  <b>FILING DATE:</b> February 9, 2004  <b>EXAMINER:</b> Tran, Mai Huong C.  <b>GROUP:</b> 2818				
<b>U.S. PATENT DOCUMENTS</b>								
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
<div style="font-size: 2em; font-family: cursive;">uht</div> <div style="border-left: 1px solid black; height: 100%; width: 1px; margin: 0 auto;"></div>	A1	2001/0003364	Sugawara <i>et al.</i>					
	A2	2002/0024395	02/28/2002	Akatsuka <i>et al.</i>				
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>				
	A4	2002/0084000	07/04/2002	Fitzgerald				
	A5	2002/0096717	07/25/2002	Chu <i>et al.</i>				
	A6	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>				
	A7	2002/0123167	09/05/2002	Fitzgerald				
	A8	2002/0123183	09/05/2002	Fitzgerald				
	A9	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>				
	A10	2002/0168864	11/14/2002	Cheng <i>et al.</i>				
	A11	2003/0003679	01/02/2003	Doyle <i>et al.</i>				
	A12	2003/0013323	01/16/2003	Hammond <i>et al.</i>				
	A13	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>				
	A14	2003/0057439	03/27/2003	Fitzgerald				
	A15	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>				
	A16	2003/0199126	10/23/2003	Chu <i>et al.</i>				
	A17	2003/0203600	10/30/2003	Chu <i>et al.</i>				
	A18	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>				
	A19	2003/0218189	11/27/2003	Christiansen				
	A20	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>				
	A21	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>				
	A22	2004/0014304	01/22/2004	Bhattacharyya				
	↓	A23	2004/0031979	02/19/2004	Lochtefeld			06/06/2003
<b>EXAMINER</b> <span style="font-family: cursive; font-size: 1.2em;">M. Huong C. Tran</span>				<b>DATE CONSIDERED</b> <span style="font-family: cursive; font-size: 1.2em;">09/30/04</span>				

<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>			
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>			
				<b>SERIAL NO.: 10/774,890</b>			
				<b>FILING DATE: February 9, 2004</b>			
				<b>EXAMINER: Tran, Mai Huong C.</b>			
				<b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MT	A24	2004/0041210	03/04/2004	Mouli			09/02/2003
	A25	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003
	A26	4,010,045	03/01/1977	Ruehrwein			
	A27	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A33	5,166,084	11/24/1992	Pfiester			
	A34	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A35	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A36	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A37	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A38	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A39	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A40	5,240,876	08/34/1993	Gaul <i>et al.</i>			
	A41	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A42	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A43	5,285,086	02/08/1994	Fitzgerald			
	A44	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A45	5,298,452	03/29/1994	Meyerson			
	A46	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
<b>EXAMINER</b> <i>Markuson</i>				<b>DATE CONSIDERED</b> <i>09/20/04</i>			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A47	5,316,958	Meyerson				
	A48	5,346,848	Gruppen-Shemansky <i>et al.</i>				
	A49	5,374,564	Bruel				
	A50	5,399,522	Ohori				
	A51	5,413,679	Godbey				
	A52	5,424,243	Takasaki				
	A53	5,426,069	Selvakumar <i>et al.</i>				
	A54	5,426,316	Mohammad				
	A55	5,442,205	Brasen <i>et al.</i>				
	A56	5,461,243	Ek <i>et al.</i>				
	A57	5,461,250	Burghartz <i>et al.</i>				
	A58	5,462,883	Dennard <i>et al.</i>				
	A59	5,476,813	Naruse				
	A60	5,479,033	Baca <i>et al.</i>				
	A61	5,484,664	Kitahara <i>et al.</i>				
	A62	5,523,243	Mohammad				
	A63	5,523,592	Nakagawa <i>et al.</i>				
	A64	5,534,713	Ismail <i>et al.</i>				
	A65	5,536,361	Kondo <i>et al.</i>				
A66	5,540,785	Dennard <i>et al.</i>					
A67	5,572,043	Shimizu <i>et al.</i>					
A68	5,596,527	Tomioka <i>et al.</i>					
✓	A69	5,617,351	Bertin <i>et al.</i>				
<b>EXAMINER</b>				<b>DATE CONSIDERED</b> 438			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
HA	A70	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A71	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A72	5,683,934	11/04/1997	Candelaria			
	A73	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A74	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A75	5,728,623	03/17/1998	Mori			
	A76	5,739,567	04/14/1998	Wong			
	A77	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A78	5,777,347	07/07/1998	Bartelink			
	A79	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A80	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A81	5,792,679	08/11/1998	Nakato			
	A82	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A83	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A84	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A85	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A86	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A87	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A88	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A89	5,943,560	08/24/1999	Chang <i>et al.</i>			
	A90	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A91	5,966,622	10/12/1999	Levine <i>et al.</i>			
✓	A92	5,998,807	12/07/1999	Lustig <i>et al.</i>			
<b>EXAMINER</b> <i>He [signature]</i>				<b>DATE CONSIDERED</b> <i>09/20/04</i>			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>11/16</i>	A93	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A94	6,030,887	02/29/2000	Desai <i>et al.</i>			
	A95	6,030,889	02/29/2000	Aulicino <i>et al.</i>			
	A96	6,033,974	03/07/2000	Henley <i>et al.</i>			
	A97	6,033,995	03/07/2000	Muller			
	A98	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A99	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A100	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A101	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A102	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A103	6,107,653	08/22/2000	Fitzgerald			
	A104	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A105	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A106	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A107	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A108	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A109	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A110	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A111	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A112	6,160,303	12/12/2000	Fattaruso			
	A113	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A114	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A115	6,191,007	02/20/2001	Matsui <i>et al.</i>			
<b>EXAMINER</b> <i>W. A. Aulicino</i>				<b>DATE CONSIDERED</b> <i>09/30/04</i>			



<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>			
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				<b>EXAMINER: Tran, Mai Huong C.</b>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MH	A116	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A117	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A118	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A119	6,207,977	03/27/2001	Augusto			
	A120	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A121	6,218,677	04/17/2001	Broekaert			
	A122	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A123	6,235,567	05/22/2001	Huang			
	A124	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A125	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A126	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A127	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A128	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A129	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A130	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A131	6,291,321	09/18/2001	Fitzgerald			
	A132	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A133	6,316,301	11/13/2001	Kant			
	A134	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A135	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A136	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A137	6,339,232	01/15/2002	Takagi			
✓	A138	6,350,993	02/26/2002	Chu <i>et al.</i>			
<b>EXAMINER</b> <i>W. Walker</i>				<b>DATE CONSIDERED</b> <i>09/30/04</i>			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A139	03/05/2002	Usenko				
	A140	04/09/2002	Nishinaga				
	A141	04/16/2002	Thornton <i>et al.</i>				
	A142	04/16/2002	Hattori <i>et al.</i>				
	A143	06/04/2002	Kubo <i>et al.</i>				
	A144	06/11/2002	Brunner <i>et al.</i>				
	A145	06/18/2002	Tezuka				
	A146	07/16/2002	Akatsuka <i>et al.</i>				
	A147	07/30/2002	Chu <i>et al.</i>				
	A148	08/06/2002	Rim				
	A149	02/18/2003	Wu <i>et al.</i>				
	A150	02/25/2003	Canaperi <i>et al.</i>				
	A151	04/29/2003	Fitzgerald				
	A152	06/03/2003	Cheng <i>et al.</i>				
	A153	06/24/2003	Fitzgerald <i>et al.</i>				
	A154	07/15/2003	Fitzgerald				
	A155	07/15/2003	Fitzgerald				
A156	08/05/2003	Fitzgerald					
A157	08/05/2003	Rim					
A158	11/11/2003	Fitzgerald					
A159	11/18/2003	Fitzgerald <i>et al.</i>					
A160	01/13/2004	Fitzgerald					
A161	03/09/2004	Fitzgerald			03/18/2003		
<b>EXAMINER</b>				<b>DATE CONSIDERED</b> 09/20/04			

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<b>U.S. PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
MH	A162	6,703,688	03/09/2004	Fitzgerald			07/16/2001		
	A163	6,709,903	03/23/2004	Christiansen			04/30/2003		
	A164	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003		
	A165	6,723,661	04/20/2004	Fitzgerald			07/16/2001		
	A166	6,724,008	04/20/2004	Fitzgerald			07/16/2001		
	A167	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002		
	A168	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
	A169	6,750,130	06/15/2004	Fitzgerald			01/07/2001		
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MH	B1	41 01 167	07/23/1992	DE				N	Y (Abstract only)
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	B8	1 020 900	07/19/2000	EP				N	Y
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	B10	2 701 599	09/01/1993	FR				Y	Y
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<b>EXAMINER</b> <i>Mai Huong C. Tran</i>					<b>DATE CONSIDERED</b> <i>09/30/04</i>				

<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>					
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>					
				<b>SERIAL NO.: 10/774,890</b>					
				<b>FILING DATE: February 9, 2004</b>					
				<b>EXAMINER: Tran, Mai Huong C.</b>					
				<b>GROUP: 2818</b>					
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
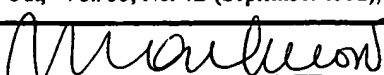
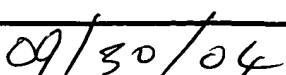
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	B45	02/071495	09/12/2002	WO				N	Y
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	B47	04/006311	01/15/2004	WO				N	Y
	B48	04/006327	01/15/2004	WO				N	Y
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
	C1	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting), pp. 761-764.							
<b>EXAMINER</b> <i>Mai Huong C. Tran</i>					<b>DATE CONSIDERED</b> <i>09/30/04</i>				

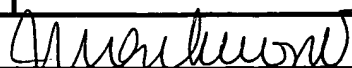
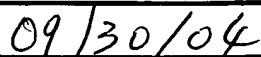
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<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Ph.D. Thesis, Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science (June 30, 1999), pp.1-154.							
	C3	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.							
	C4	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMO transistors," <u>Modern Physics Letters B</u> , Vol. 15, No. 28-29 (December 2001), abstract.							
	C5	Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12 <sup>th</sup> IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210.							
	C6	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 $\mu$ m bulk CMOS experimental study," IEEE, (1996), pp. 21.2.1-21.2.4.							
	C7	Bruehl <i>et al.</i> , "@SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.							
	C8	Bruehl, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 31, No. 14 (July 6, 1995), pp. 1201-1202.							
	C9	Buefler <i>et al.</i> , "Hole transport in strained Si <sub>1-x</sub> Ge <sub>x</sub> alloys on Si <sub>1-y</sub> Ge <sub>y</sub> substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.							
	C10	Burghartz <i>et al.</i> , "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996), pp. 100-104.							
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<b>EXAMINER</b>		M. Huong C. Tran			<b>DATE CONSIDERED</b>		09/30/04		

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✓	C12	Carlin <i>et al.</i> , "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," <i>IEEE</i> (2000), pp. 1006-1011.							
	C13	Chang <i>et al.</i> , "Selective Etching of SiGe/Si Heterostructures," <i>Journal of the Electrochemical Society</i> , No. 1 (January 1991), pp. 202-204.							
	C14	Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <i>IEEE Electron Device Letters</i> , Vol. 22, No. 7 (July 2001), pp. 321-323.							
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	C20	Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <i>Journal of Electronic Materials</i> , Vol. 23, No. 6 (June 1994), pp. 493-496.							
	C21	Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <i>Journal of Applied Physics</i> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252.							
✓	C22	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <i>Journal of Applied Physics</i> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250.							
<b>EXAMINER</b>		Muller			<b>DATE CONSIDERED</b>		09/30/04		

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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
MA	C23	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.							
	C24	Fitzgerald <i>et al.</i> , "Relaxed Ge <sub>x</sub> Si <sub>1-x</sub> structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>Journal of Vacuum Science and Technology</u> , (July/August 1992), pp. 1807-1819.							
	C25	Fitzgerald <i>et al.</i> , "Totally Relaxed Ge <sub>x</sub> Si <sub>1-x</sub> Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813.							
	C26	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.							
	C27	Godbey <i>et al.</i> , (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si <sub>0.7</sub> Ge <sub>0.3</sub> Layer as an Etch Stop," <u>Journal of the Electrical Society</u> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.							
	C28	Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632.							
	C29	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (2002), pp. 4891-4899.							
	C30	Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.							
	C31	Hackbarth <i>et al.</i> , "Alternatives to Thick MBE-Grown Relaxed SiGe Buffers," <u>Thin Solid Films</u> , Vol. 369 (2000), pp. 148-151.							
	C32	Hackbarth <i>et al.</i> , "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999), pp. 734-738.							
	C33	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (1999), pp. 199-202.							
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<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
	C34	Herzog <i>et al.</i> , "SiGe-based FETs: Buffer Issues and Device Results," <u>Thin Solid Films</u> , Vol. 380, No. 1-2 (December 12, 2000), pp. 36-41.							
	C35	Höck <i>et al.</i> , "Carrier mobilities in modulation doped Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998), pp. 141-144.							
	C36	Höck <i>et al.</i> , "High hole mobility in Si <sub>0.17</sub> Ge <sub>0.83</sub> channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922.							
	C37	Höck <i>et al.</i> , "High performance 0.25 $\mu$ m <i>p</i> -type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998), pp. 1888-1889.							
	C38	Hsu <i>et al.</i> , "Surface morphology of related Ge <sub>x</sub> Si <sub>1-x</sub> films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295							
	C39	Huang <i>et al.</i> , "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.							
	C40	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036.							
	C41	Huang <i>et al.</i> , (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology, Digest of Technical Papers</u> , pages 57-58							
	C42	IBM Technical Disclosure Bulletin, "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates," Vol. 32, No. 8A (January 1990), pp. 330-331.							
	C43	IBM Technical Disclosure Bulletin, "2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," Vol. 35, No. 4B (September 1992), pp. 136-140.							
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MAA	C44	Ishikawa <i>et al.</i> , "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," Proceedings of the 1997 IEEE International SOI Conference (October 1997), pp. 16-17.							
	C45	Ishikawa <i>et al.</i> , "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.							
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	C47	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," International Electron Devices Meeting, Washington, D.C. (December 10, 1995), pp. 20.1.1-20.1.4.							
	C48	Kearney <i>et al.</i> , "The effect of alloy scattering on the mobility of holes in a Si <sub>1-x</sub> Ge <sub>x</sub> quantum well," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 174-180.							
	C49	Kim <i>et al.</i> , "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998), pp. 293-295.							
	C50	Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si <sub>0.4</sub> Ge <sub>0.6</sub> p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112.							
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